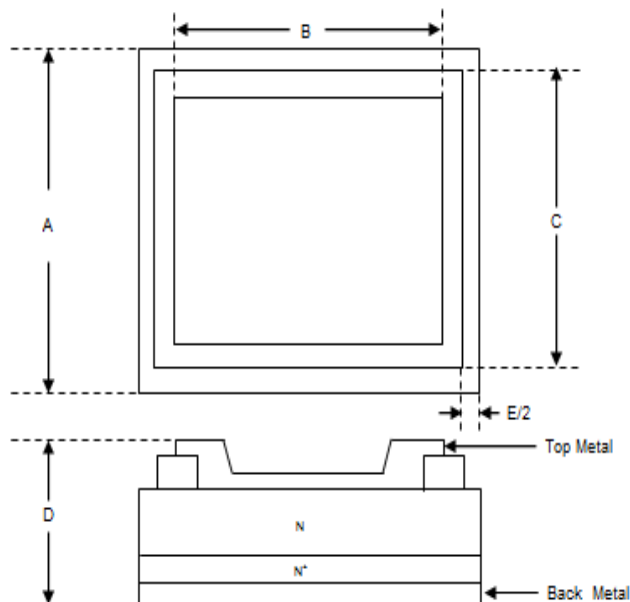


### Planar MOS-Controlled Diode Wafer (PMCD)



| Item                   | Dimensions |       |
|------------------------|------------|-------|
|                        | um         | mil   |
| Die Size (A)           | 3011       | 118   |
| Top Metal Pad Size (B) | 2855       | 112.4 |
| Passivation Seal (C)   | 2941       | 115.8 |
| Wafer Thickness (D)    | 260        | 10.2  |
| Scribe Line Width (E)  | 70         | 2.76  |
| Other Informations     |            |       |
| Wafer Size             | 6"         |       |
| Gross Die              | 1720       |       |
| Top Metal              | Al         |       |
| Back Metal             | Ag         |       |

| Electrical Characteristics @TA=25°C   |           |                           |                     |         |
|---|-----------|---------------------------|---------------------|---------|
| Item  | Symbol    | Spec. Limit               | Die Sort            | Unit    |
| Maximum Repetitive Peak Reverse Voltage<br>@0.5mA   | $V_{RRM}$ | 60                        | 64                  | V       |
| Maximum Average Forward Rectified Current   | $I_O$     | 20                        | -                   | A       |
| Forward Voltage Drop,<br>@ $I_F=3A$<br>@ $I_F=10A$<br>@ $I_F=15A$<br>@ $I_F=20A$                  | $V_F$     | -<br>0.48<br>0.54<br>0.59 | 0.37<br>-<br>-<br>- | V       |
| Maximum Reverse Current at Rated $V_{RRM}$  | $I_R$     | 170                       | 150                 | $\mu A$ |
| Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC Method) | $I_{FSM}$ | 300                       | -                   | A       |
| Operating Temperature Range   | $T_J$     | -50 to +150               | -                   | °C      |
| Storage Temperature Range   | $T_{STG}$ | -50 to +150               | -                   | °C      |